

Thermal lensing in high-power ridge-waveguide lasers

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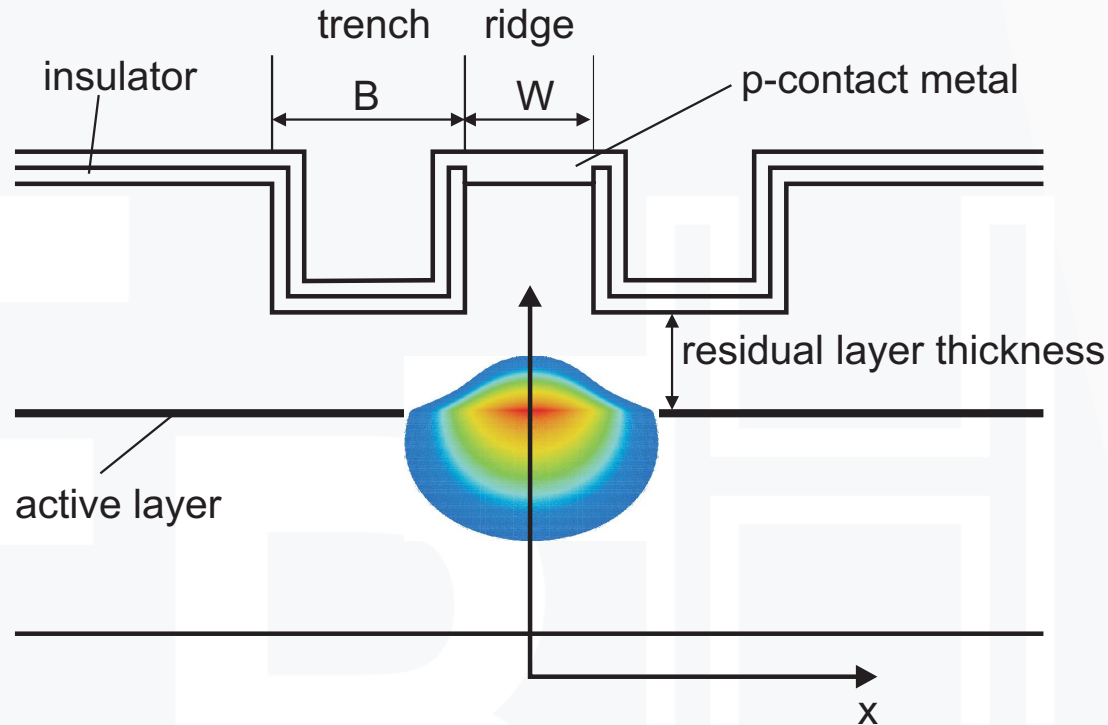
Outline

- motivation and laser structure
- experimental results
- theoretical model
- simulation results
- conclusions

Motivation

- fundamental–spatial mode diode lasers with an output power in the 1–W range of interest for a variety of applications
- requires narrow lateral waveguide defined by small effective index step to cut–off higher order modes
- at higher output power appearance of instabilities like
 - kinks in light–current characteristics
 - beam steering
 - appearance of higher order modes
- possible reasons:
 - carrier–induced index suppression
 - **thermal lensing**
 - spatial hole burning

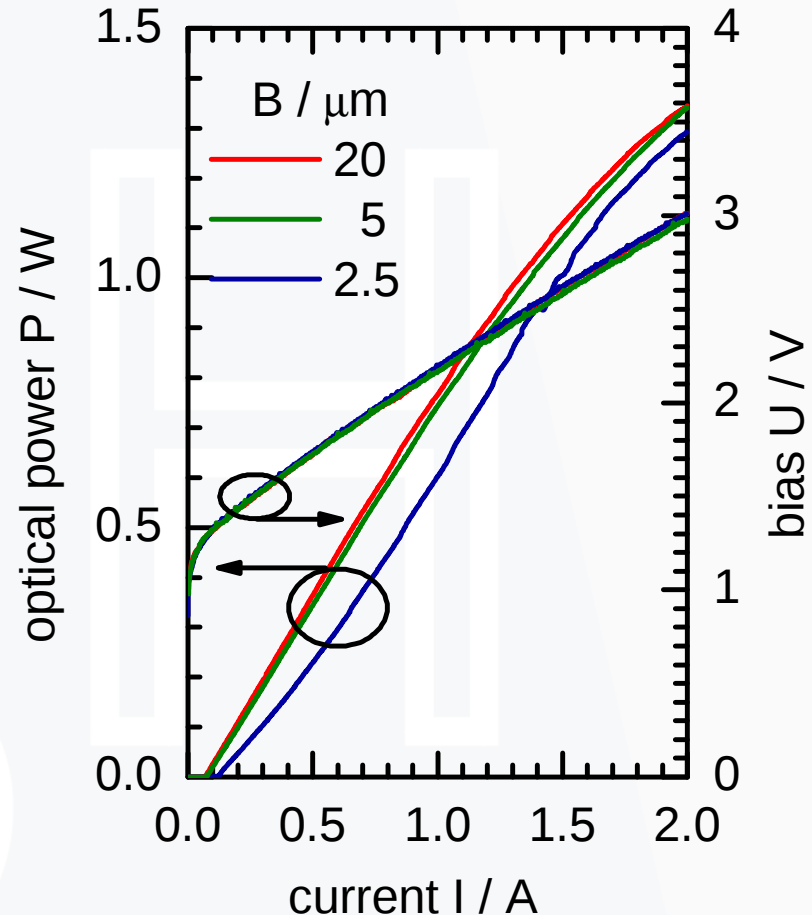
Schematic cross-sectional view of RW devices



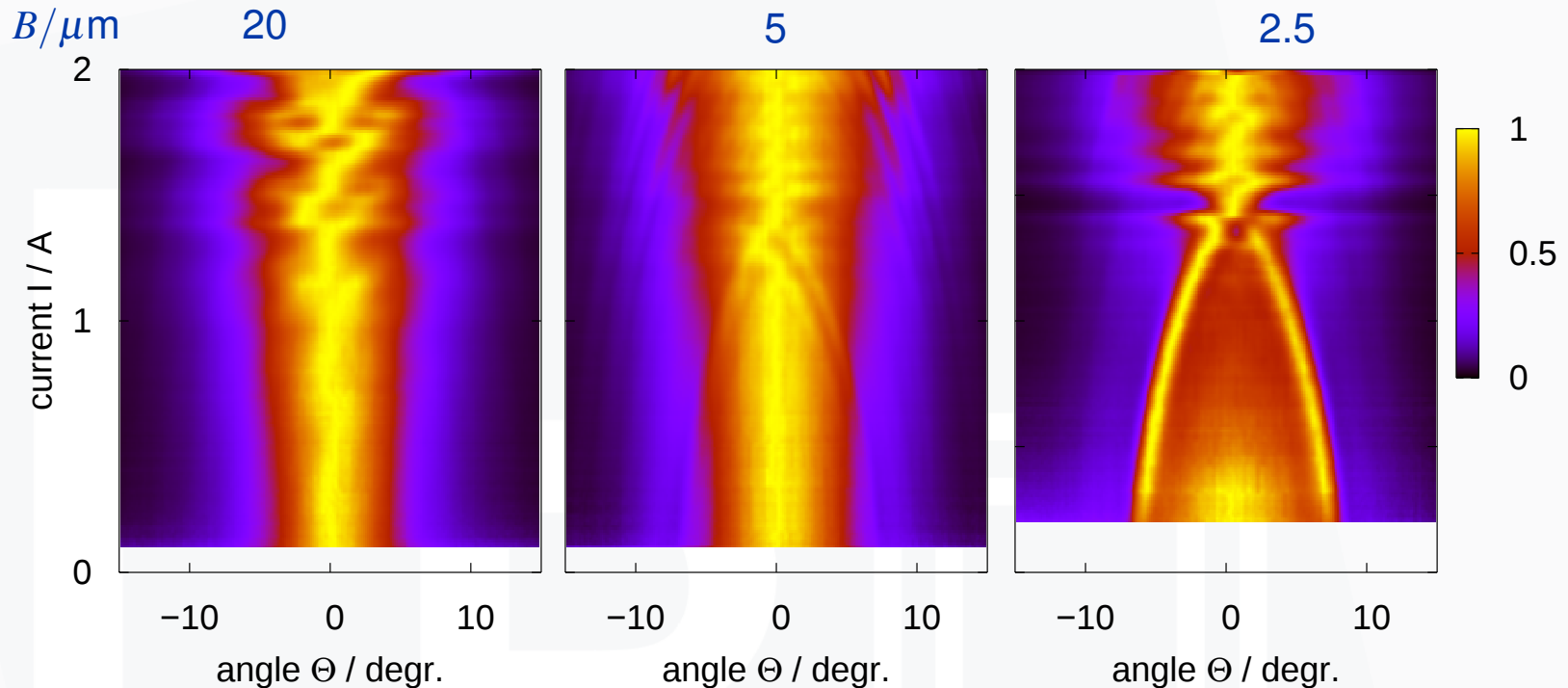
- finite trench width $\Rightarrow$ radiation leaks into the outer high-index regions
- radiation loss rises with mode number $\Rightarrow$ stabilization of 0th order mode
- anti-index guiding $\Rightarrow$ sensitive to thermal lensing effect

Experimental light–current characteristics

- cavity length $L = 3.9$ mm
- ridge width $W = 2.8$ μm
- emission wavelength around $\lambda = 1064$ nm
- output power $P > 1.3$ W at $I = 2$ A
- only small difference in the characteristics for trench widths $B = 20$ μm and $B = 5$ μm
- strong increase of threshold current and decrease of slope efficiency slightly above threshold for $B = 2.5$ μm



Experimental lateral far-field intensity profiles



- strong dependence of far-field profiles on trench width
- $B = 5 \mu\text{m}$: much more stable far-field compared to $B = 20 \mu\text{m}$
- $B = 2.5 \mu\text{m}$: double peaked far-field, peaks joining around $I = 1.4 \text{ A}$

Theoretical model: Optics

effective index method for calculating lateral field profile $\Phi(x)$ and complex propagation constant β

$$\frac{d^2\Phi}{dx^2} = [\beta^2 - k_0^2 \epsilon_{\text{eff}}(x)] \Phi(x)$$

boundary conditions

$$\left. \frac{d\Phi}{dx} \right|_{x=0} = 0 \quad (\text{even modes})$$

$$\lim_{x \rightarrow \infty} \Phi(x) \propto e^{-i\sqrt{k_0^2 \epsilon_{\text{eff}}(x_c) - \beta^2} x} \quad \text{with} \quad \text{Re} \sqrt{k_0^2 \epsilon_{\text{eff}}(x_c) - \beta^2} > 0$$

(outgoing wave)

far field

$$S_{\text{FF}}(\Theta) = \left| \int_0^\infty \Phi(x) e^{k_0 \sin(\Theta)x} dx \right|^2$$

Complex effective dielectric function

$$\epsilon_{\text{eff}}(x) = 2n_{\text{eff},0} \left[\frac{n_{\text{eff},0}}{2} + \Delta n_{\text{eff}}(x) + \Delta n_N(x) + \Delta n_T(x) + i \frac{g_{\text{eff}}(x)}{2k_0} \right]$$

background effective index

$n_{\text{eff},0}$

built-in effective index step

$\Delta n_{\text{eff}}(x)$

step-wise constant

carrier-density dependent part

$$\Delta n_N(x) = \Gamma_{\text{AZ}} \frac{\partial n}{\partial N} N < 0$$

step-wise constant

temperature dependent part

$$\Delta n_T(x) = \frac{\partial n}{\partial T} T(I, x) > 0$$

effective gain

$g_{\text{eff}}(N)$

step-wise constant

In the model, ϵ_{eff} depends on current only via temperature T .

Theoretical model: Heat I

effective heat conduction equation for lateral relative temperature profile $T(x)$
(temperature difference to heat sink temperature)

$$\kappa \frac{d^2 T}{dx^2} = -q(x) + \gamma T(x)$$

boundary conditions

$$\left. \frac{dT}{dx} \right|_{x=0} = 0 \quad \text{and} \quad \lim_{x \rightarrow \infty} T(x) = 0$$

dissipated power density within active stripe obtained from experimental light-voltage-current $P - U - I$ characteristics

$$q(I) = \frac{U(I)I - P(I)}{dWL}$$

Theoretical model: Heat II

temperature relaxation parameter γ determined from the condition

$$\frac{2}{W} \int_0^{W/2} T(x, I_0) dx = \left[\frac{\partial \lambda}{\partial T} \right]^{-1} [\lambda(I_0) - \lambda(0)]$$

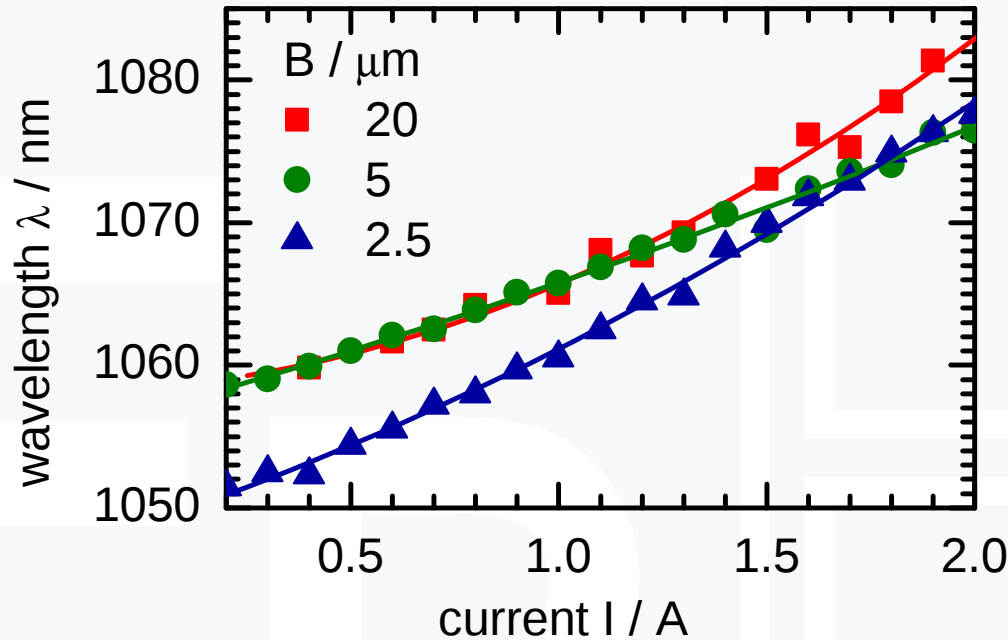
calculated average temperature within the active stripe

temperature rise determined from the experimental wavelength shift

dependence of emission wavelength on injection current

$$\lambda(I) = a + bI + cI^2$$

Experimental wavelength–current characteristics



parameters of $\lambda(I)$ and γ determined at $I_0 = 1 \text{ A}$

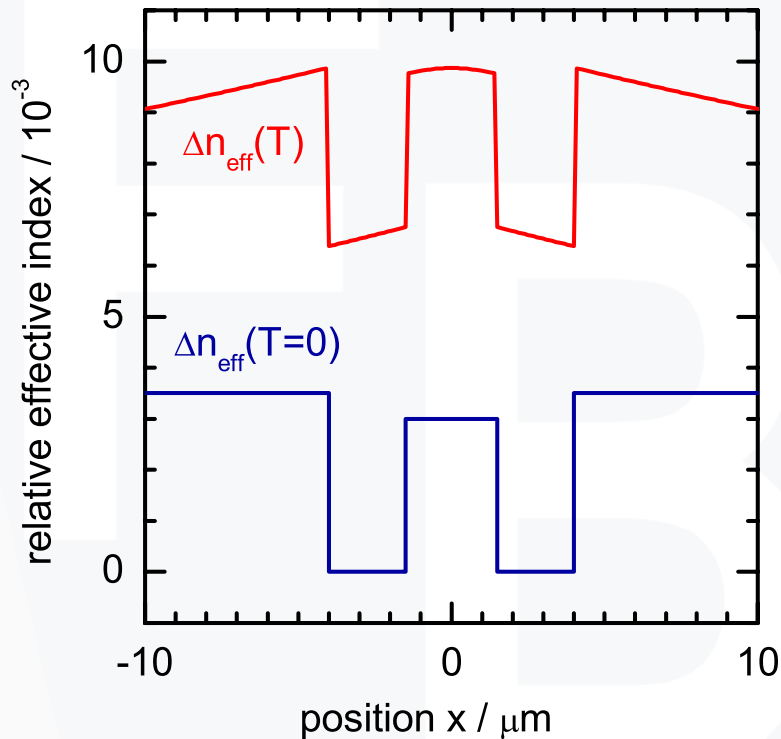
$B / \mu\text{m}$	a / nm	b / nmA^{-1}	c / nmA^{-2}	$\gamma / 10^{11} \text{KW}^{-1} \text{m}^{-2}$
20	1058.4	2.4	4.9	1.9
5	1056.7	8.2	0.9	1.2
2.5	1048.9	9.8	2.5	0.8

Model parameters

parameter	value
d	$2 \mu\text{m}$
W	$3 \mu\text{m}$
L	$3900 \mu\text{m}$
κ	$160 \text{ WK}^{-1}\text{m}^{-1}$
$\frac{\partial n}{\partial T}$	$2.5 \times 10^{-4} \text{ K}^{-1}$
$\frac{\partial \lambda}{\partial T}$	0.45 nmK^{-1}
$n_{\text{eff},0}$	3.33
Δn_{eff}	ridge: 3.5×10^{-3} trench: 0
Δn_N	outside: 3.5×10^{-3} ridge: -5×10^{-4} trench: 0
g_{eff}	outside: 0 ridge: 20 cm^{-1} trench: 0
	outside: -20 cm^{-1}

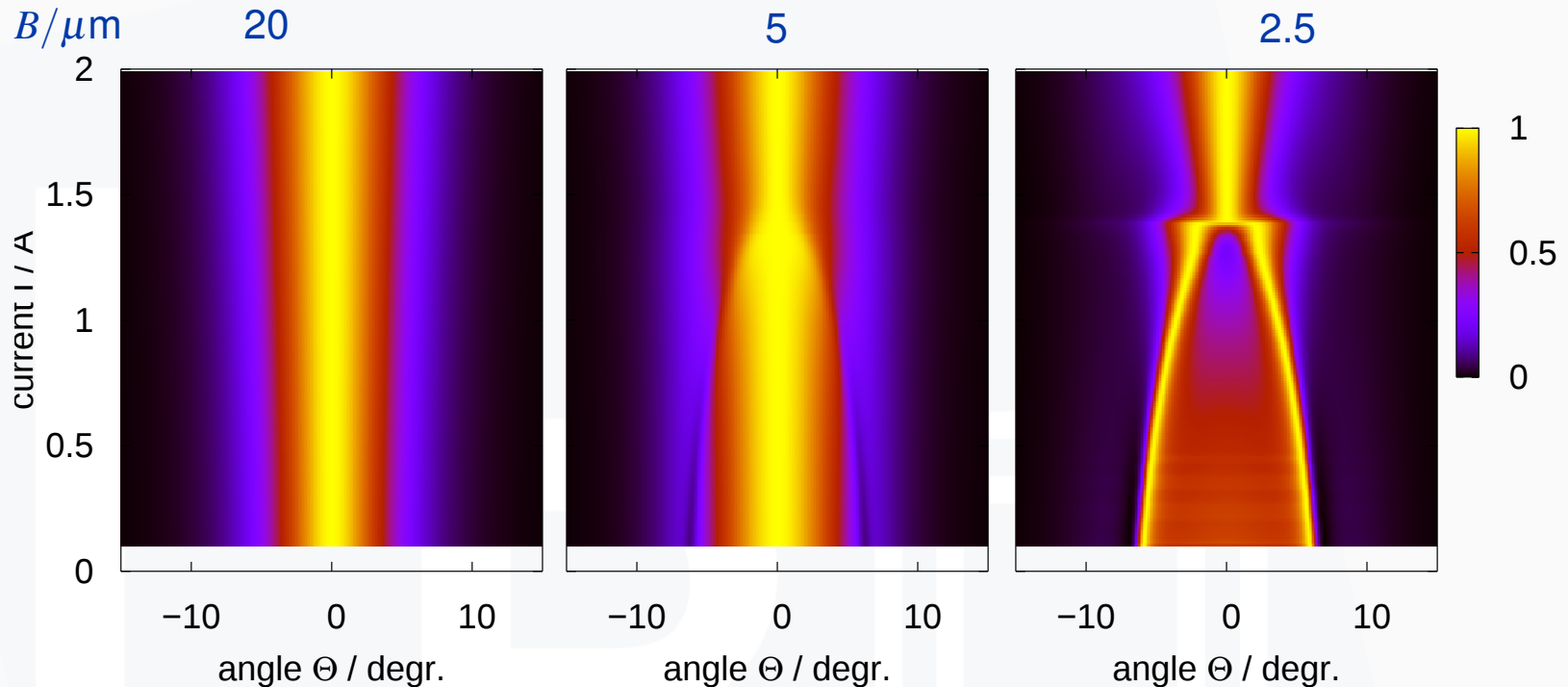
Model parameters

effective-index profiles without and with
heating: anti- vs. real-index guiding

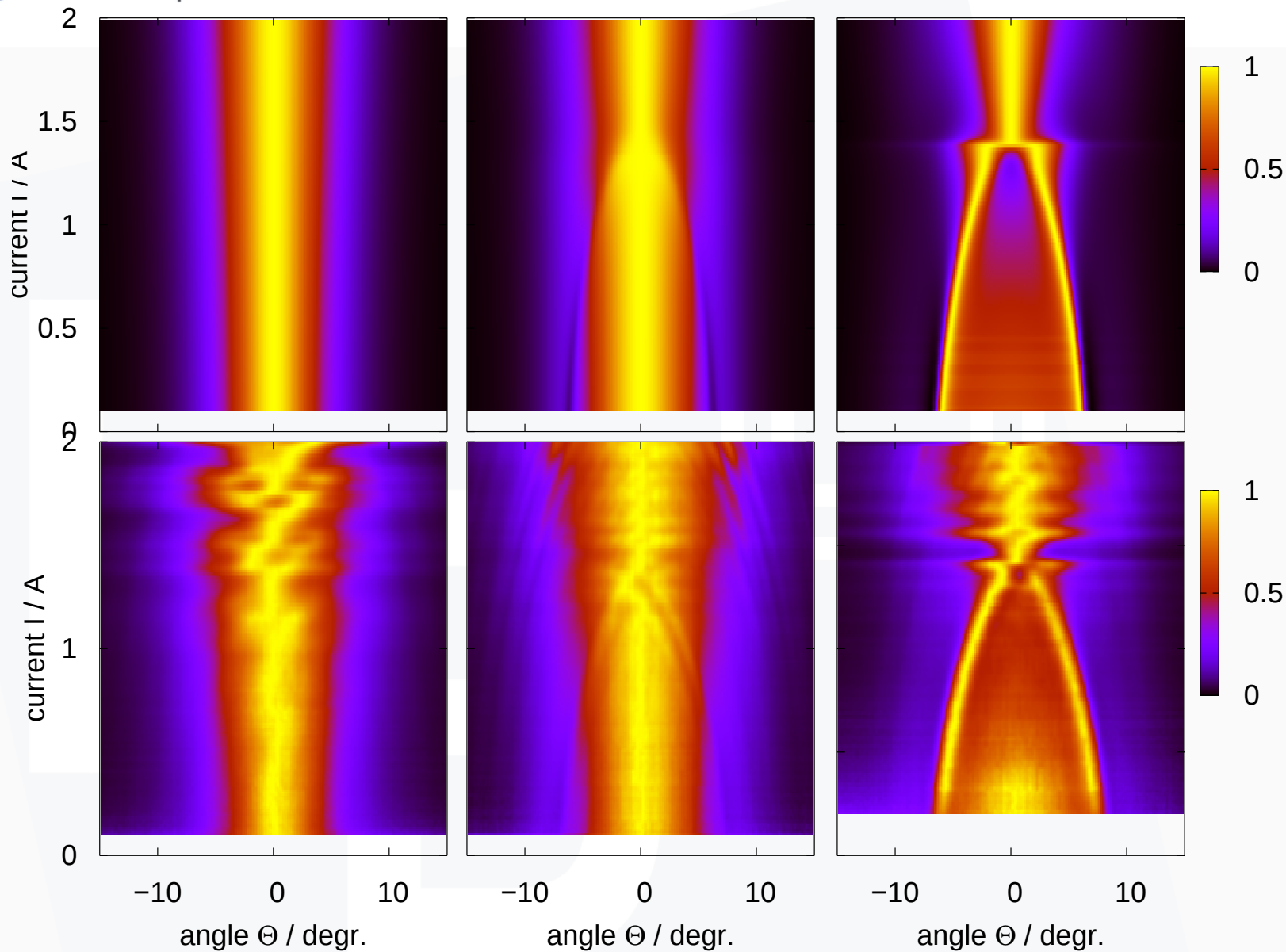


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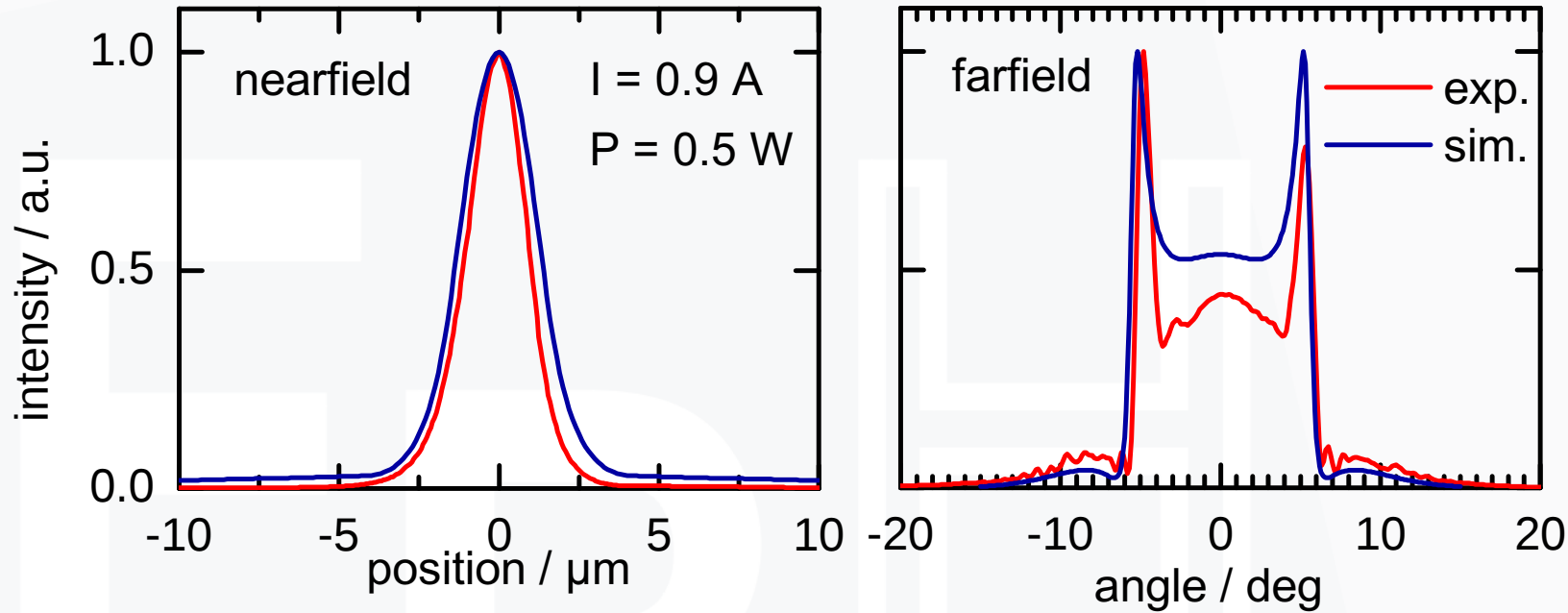
Calculated lateral far-field intensity profiles



- same dependence on trench width and current as measured
- $B = 2.5 \mu\text{m}$: far-field peaks joining at $I = 1.4 \text{ A}$ due to thermal lensing



Measured and calculated near- and far-field profiles



- good agreement for both near- and far-field profiles despite the simple model used
- parameters and model o.k.

Conclusions

- thermal lensing contributes significantly to lateral waveguiding in high-power narrow-stripe lasers
- for $P > 1$ W thermal lensing governs lateral waveguiding
 - associated with pronounced far-field instabilities visible in the experimental profiles as current is varied
 - possibly caused by coherent superposition of fundamental and higher order modes
- very stable far-field for trench width $B = 5 \mu\text{m}$
- minimization of thermal-lensing effect crucial for increase of fundamental-spatial mode output power